Micron Announces Availability of 30nm DDR3L-RS Products to Enable a New Generation of Intel Ultrabook(TM) and Ultrathin Computing Devices

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BOISE, Idaho, Sept. 18, 2012 (GLOBE NEWSWIRE) -- Micron Technology, Inc. (Nasdaq:MU), one of the world's leading providers of advanced semiconductor solutions, today announced high-volume availability of 30-nanometer (nm) reduced-power DDR3L-RS SDRAM for ultrathin computing devices and tablets. The 2-gigabit (Gb) and 4Gb solutions reduce power consumption in standby to provide longer battery life, while maintaining the high performance and cost effectiveness of PC DRAM.

"Micron has been one of the leaders in the development and commercialization of DDR3L-RS and the introduction of its 30nm product is confirmation of this," said Mike Howard, senior principal analyst, DRAM and Memory at IHS iSuppli. "DDR3L-RS is an excellent option for customers who have tight power budgets and need high performance at a competitive price. We expect many of the next-generation ultrathin platforms to take advantage of DDR3L-RS."

Previously announced as "DDR3Lm," these devices improve overall system power consumption by reducing self refresh power (IDD6), enabling Micron to provide chipset vendors, enablers and electronics manufacturers with best-in-class, reduced-power memory that offers the same performance, quality and reliability as standard DRAM. DDR3L-RS meets the expanding needs of today's ultrathin computing and tablet markets and paves the way for enhanced features and capabilities in products like the Intel Ultrabook device.

"The feedback from our customers about this new category of DRAM has been extremely positive," said Robert Feurle, vice president for Micron's DRAM marketing. "We are pleased to be the leading provider of DRAM solutions which are enabling the introduction of ultrathin notebooks and tablets that are thinner, faster and run longer on a single charge."

Micron's milestone of being the first vendor with DDR3L-RS products to be validated at Intel is affirmed in a web posting on Intel's site.

"Micron was the first DRAM supplier validated on the Ivy Bridge platform with DDR3L-RS, setting the industry standard for reduced standby PC DRAM," said Geof Findley, Memory Enabling Senior Manager at Intel.

In addition to the 2Gb and 4Gb devices, Micron has begun sampling 8Gb x 32 DDR3L-RS and is delivering samples of 8Gb x 16 DDR3L-RS; production is slated for December 2012. These products offer additional system design flexibility by reducing board space and increasing density. Additional power and footprint savings are expected with the launch of DDR4-RS in early 2013.

With this announcement Micron is well-positioned to support the growth of ultrathin applications with its broad portfolio of DRAM, NAND, NOR and SSD solutions. For more information, please visit www.micron.com.

The Micron Technology, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6950

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